

CLAIMS

Sub B.1.7
1. An array of photodiodes made of regions of a second conductivity type formed in a semiconductive region of a first conductivity type, divided into three interleaved sub-arrays, all the photodiodes of a same sub-array being coated with a same interference filter including at least one
5 insulating layer of determined thickness coated with at least one conductive layer, wherein said conductive layers are electrically connected to the semiconductive region of a first conductivity type.

2. The array of photodiodes of claim 1, wherein the electric connection is indirect.

Sub C.1.7
3. The array of photodiodes of claim 1, wherein the semiconductor substrate is a single-crystal silicon substrate, and the interference filter includes a silicon oxide layer formed above the substrate and a conductive polysilicon layer formed above the silicon oxide layer.

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